NSN 5961-00-110-7648

Thyristor Semiconductor Device - Page 1 of 2

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Inclosure Material:

Metal

Overall Length:

Between 0.300 inches and 0.400 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Anode

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

Between 0.424 inches and 0.437 inches

Thread Size:

0.190 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

720.0 breakdown voltage, emitter-to-base, collector open and 10.0 peak negative gate voltage and 600.0 reverse voltage, peak

Current Rating Per Characteristic:

2.00 amperes forward current, total rms blank and 4.70 amperes forward current, total rms megahertz and 60.00 amperes forward current, total rms watts

Power Rating Per Characteristic:

5.0 watts small-signal input power, common-collector blank

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npnp

Test Data Document:

97942-580r299 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Thread Series Designator:

Unf

Terminal Type And Quantity:

2 tab, solder lug and 1 threaded stud

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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